EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L2	12064	"Hewlett-Packard Development ". asn.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/23 07:32
L3	53	"6165911"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/23 07:32
L4	17	2 and L3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/23 07:32
L5	456	nano?imprint lithography	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/23 07:33
L6	17	L5 and (silicon near substrate) and (imprint pattern)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/23 07:33
L7	0	2 and L6	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/23 07:33
L8	15	2 and 5	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/23 07:33
L9	5	L2 and (silicon near substrate) and (imprint pattern)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/23 07:34

S1	2	("5948470").PN. or ((2002/042027) or (2002/005391)).CCLS.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/05/19 12:45
S2	0	(2002/042027).CCLS.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/05/19 13:35
S3	0	2002/042027	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/19 13:35
S4	0	2002/042027	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/19 13:36
S5	0	(stephen chou).inv.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/19 13:36
S6	4	("2002042027").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/05/19 13:37
S7	89	(stephen near chou).inv.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/19 13:43
S8	0	S7 and @pd="02200411"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/19 13:44
S9	0	(2002/0005391).CCLS.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/05/19 13:46

S10	0	(2002/005391).CCLS.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/05/19 13:46
S11	0	2002/005391	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/19 13:46
S12	0	2002/0005391	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/19 13:47
S13	0	thurn-albrect.inv.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/19 13:47
S14	10	(thurn-albrecht).inv.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/19 13:48
S15	75	"5948470"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/19 13:50
S16	2	("5948470").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/05/19 13:50
S17	0	(wo01/33300).CCLS.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/05/19 13:50
S18	20	01/33300	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/19 13:51

S19	0	("wo20010500").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/05/19 13:52
S20	117005	"20010500"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/19 13:53
S21	0	wo?20010500	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/19 13:53
S22	0	wo20010500	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/19 13:53
S23	2	("7082876").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/05/19 13:54
S24	0	WO "20010500"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/19 14:26
S25	0	method of reducing pattern distortions during imprint lithography	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/19 14:30
S26	15	reducing pattern distortions during imprint lithography	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/19 14:31
S27	1	wo-0133300-$.did.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/19 14:32

S28	2	de-10030016-$.did.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/19 14:34
S29	32985954	@pd<"20031112"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/20 10:04
S30	1308003	template or mold	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/20 10:05
S31	7481	S30 near substrate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/20 10:06
S32	289533	silicon near3 substrate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/20 10:06
S33	436	S31 with (polymer or pmma or pmgi or photoresist)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/20 10:07
S34	168	S29 and S30 and S33	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/20 10:07
S35	798153	nanometer or nm or nanoprint or nanopattern	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/20 10:09
S36	48	S34 and S35	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/20 10:09

S37	28	S29 and S33 and S32 and S35	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/20 10:14
S38	3465	(ge or germanium) near semiconductor	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/20 13:06
S39	126033	semiconductor adj layer	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/20 13:06
S40	207948	silicon near substrate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/20 13:07
S41	798313	nm or nanometer or nanoprint or nanoimprint or nanopattern	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/20 13:08
S42	32985954	@pd<"20031112"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/20 13:09
S43	3465	(ge or germanium) near semiconductor	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/20 13:11
S44	126033	semiconductor adj layer	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/20 13:11
S45	798313	nm or nanometer or nanoprint or nanoimprint or nanopattern	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/20 13:11

S46	0	S43 and S44 and s "40" and S45	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/20 13:11
S47	207948	silicon near substrate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/20 13:11
S48	322	S43 and S44 and S47 and S45	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/20 13:11
S49	32985954	@pd< "20031112"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/20 13:12
S50	93	S48 and S49	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/20 13:12
S51	28	S50 and (pmma or polymer or photoresist or pmgi)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/20 13:13
S52	226110	template	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/20 14:32
S53	55209	S52 and "43" and "45" and "51"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/20 14:33
S54	3465	(ge or germanium) near semiconductor	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/20 14:34

S55	126033	semiconductor adj layer	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/20 14:34
S56	798313	nm or nanometer or nanoprint or nanoimprint or nanopattern	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/20 14:34
S57	207948	silicon near substrate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/20 14:34
S58	322	S54 and S55 and S57 and S56	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/20 14:34
S59	32985954	@pd<"20031112"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/20 14:34
S60	93	S58 and S59	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/20 14:34
S61	28	S60 and (pmma or polymer or photoresist or pmgi)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/20 14:34
S62	0	S52 and S54 and S56 and S61	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/20 14:34
S63	463	(silicon near substrate) and (polymer or pmma or pmgi or photoresist) and (semiconductor near (ge or germanium))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/20 14:36

S64	159	S63 and S59	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/20 14:37
S65	13	S60 and (pmma or polymer or pmgi)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/20 14:47
S66	346	S59 and S56 and S52 and S57 and germanium	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/05/20 14:48
S67	4630	(((nano?imprint$3) or (nano imprint $3) or (imprint adj lithograp$6)) or nanolithograp$5 or (nano?lithogra $6))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/21 10:34
S68	1602236	germanium or ge	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/21 10:35
S69	268466	(pmma or polymethylmeth$ or pmgi or polymethylgluta$ or az5214e or photoresist)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/21 10:38
S70	1112	S67 and S68	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/21 10:38
S71	101	S67 same S68	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/21 10:38
S72	1540	S67 and S69	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/21 10:41

S73	480	S67 same S69	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/21 10:42
S74	26586	S68 and S69	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/21 10:42
S75	3507	S68 same S69	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/21 10:42
S76	10	S71 and S73 and S75	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/21 10:42
S77	65	shunpu.inv.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/21 11:21
S78	19543	template.ti.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/21 11:21
S79	4	S78 and S77	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/21 11:21
S80	3	("4407695" | "4512848" | "4801476").PN.	US-PGPUB; USPAT; USOCR	ADJ	ON	2008/07/21 12:38
S81	34806	germanium with (aluminum or al or indium or gold)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/21 14:15
S82	5375	(germanium with (aluminum or al or indium or gold)) with semiconductor	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/21 14:16

S83	30322507	@ad<"20050513"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/21 14:20
S84	3671	S82 and S83	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/21 14:20
S85	92	S84 and substrate and pmma	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/21 14:20
S86	505	((((germanium with (aluminum or al or indium or gold)) with semiconductor) with substrate) and S69	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/21 14:31
S87	938302	"427".clas. or "428".clas. or "430". clas. or "425".clas. or "264".clas. or "156".clas.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/21 14:35
S88	572282	S83 and S87	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/21 14:36
S89	2	("4512848").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/21 14:41
S90	483	photoresist and template and silicon and germanium and S69 and pattern and (nanometer or angstrom or nm)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/21 15:03
S91	108	S90 and S88	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/21 15:04

S92	108	S91 and germanium	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/21 15:13
S93	268466	(pmma or polymethylmeth$ or pmgi or polymethylgluta$ or az5214e or photoresist)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/21 17:12
S94	30322507	@ad< "20050513"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/21 17:12
S95	938302	"427".clas. or "428".clas. or "430". clas. or "425".clas. or "264".clas. or "156".clas.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/21 17:12
S96	572282	S94 and S95	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/21 17:12
S97	483	photoresist and template and silicon and germanium and S93 and pattern and (nanometer or angstrom or nm)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/21 17:12
S98	108	S97 and S96	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/21 17:12
S99	108	S98 and germanium	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/21 17:12
S100	34	S99 and (imprint with lithography)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/21 17:12

S101	34	(US-20060076717-$ or US-20060062867-$ or US-20060035164-$ or US-20040141168-$ or US-20040124566-$ or US-20040086793-$ or US-20040053146-$ or US-20040022888-$ or US-20040021254-$ or US-20040007799-$ or US-20030205658-$ or US-20030205657-$ or US-20020115002-$ or US-20020098426-$ or US-20020094496-$ or US-20020093122-$).did. or (US-7374968-$ or US-7338275-$ or US-7229273-$ or US-7179079-$ or US-7140861-$ or US-7132225-$ or US-7077992-$ or US-7070405-$ or US-7037639-$ or US-7027156-$ or US-6954275-$ or US-6932934-$ or US-6926921-$ or US-6921615-$ or US-6919152-$ or US-6916585-$ or US-6916584-$ or US-6696220-$).did.	US-PGPUB; USPAT	ADJ	ON	2008/07/21 17:28
S102	34	S101 and germanium	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/21 17:29
S103	1	S102 not (silicon adj germanium)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/21 17:31
S104	1	S103 and germanium and S93 and S97	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/21 17:35
S105	13	("20030213382" | "20040163758" | "5512131" | "6060121" | "6365059" | "6407443" | "6518194" | "6547940" | "6599824" | "6709929" | "6755984" | "6764833" | "7060625").PN.	US-PGPUB; USPAT; USOCR	ADJ	ON	2008/07/22 07:59
S106	5	"6506660"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/22 08:08

S107	34	(US-20060076717-$ or US-20060062867-$ or US-20060035164-$ or US-20040141168-$ or US-20040124566-$ or US-20040086793-$ or US-20040053146-$ or US-20040022888-$ or US-20040021254-$ or US-20040007799-$ or US-20030205658-$ or US-20030205657-$ or US-20020115002-$ or US-20020098426-$ or US-20020094496-$ or US-20020093122-$).did. or (US-7374968-$ or US-7338275-$ or US-7229273-$ or US-7179079-$ or US-7140861-$ or US-7132225-$ or US-7077992-$ or US-7070405-$ or US-7037639-$ or US-7027156-$ or US-6954275-$ or US-6932934-$ or US-6926921-$ or US-6921615-$ or US-6919152-$ or US-6916585-$ or US-6916584-$ or US-6696220-$).did.	US-PGPUB; USPAT	ADJ	ON	2008/07/22 09:59
S108	34	S107 and germanium	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/22 09:59
S109	1666	germanium with sputter$4	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/22 10:17
S110	26	S109 and silicon and pmma	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/22 10:17
S111	34	S107 and nm	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/22 12:33
S112	16	S107 and (layer with nm)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/22 12:34

S113	7	S107 and ((thick or thickness) with nm)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/22 12:37
S114	0	S107 and ((thick or thickness) with (mask or polymer))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/22 12:39
S115	0	S107 and ((thick or thickness) with (resist))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/22 12:39
S116	4	S107 and ((thick or thickness) with ($resist))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/22 12:40
S117	3	S107 and pmma	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/22 13:03
S118	1	S107 and polymethylmethacrylate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/22 13:04
S119	25	((US-20020042027-$ or US-20020005391-$ or US-20030205658-$ or US-20030205657-$ or US-20050281982-$ or US-20050221218-$ or US-20040141168-$ or US-20040124566-$ or US-20040086793-$ or US-20040053146-$ or US-20040053009-$ or US-20020168592-$ or US-20020115002-$ or US-20020094496-$ or US-20060035164-$ or US-20040170925-$).did. or (US-5948470-$ or US-6753130-$ or US-4512848-$ or US-7374968-$ or US-7060625-$ or US-6755984-$ or US-6365059-$ or US-5512131-$).did. or (US-5948470-$ or WO-0133300-A-$ or DE-10030016-A-$).did.	US-PGPUB; USPAT; DERWENT	ADJ	ON	2008/07/22 13:07

S120	10	SI19 and pmma	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/22 13:08
S121	23	SI19 and nm	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/22 13:15
S122	1	("20030071016").PN.	US-PGPUB; USPAT; USOCR	ADJ	ON	2008/07/22 16:23
S123	199	(lee near heon).inv.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/22 16:42
S124	15	S123 and silicon and substrate and pattern and imprint	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/22 16:43
S125	177981	"430".clas. or "216".clas.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/22 16:47
S126	533	S125 and silicon and substrate and pattern and imprint	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/22 16:47
S127	190	S126 and template	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/22 16:48
S128	32	S127 and imprint pattern	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/22 16:49
S129	5	2003/0071016	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/22 16:52

S130	2	"20030071016"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/22 16:52
S131	456	nano?imprint lithography	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/22 17:00
S132	17	S131 and (silicon near substrate) and (imprint pattern)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/22 17:01
S133	53	"6165911"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/22 17:05
S134	4	"6673714"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/07/22 17:07

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